



GaN-HEMT 30W

EGN21C030MK

High Voltage - High Power GaN-HEMT

FEATURES

- High Voltage Operation : $V_{DS}=50V$
- High Power : 45.0dBm (typ.) @ P_{sat}
- Power Gain : 19dB(typ.) @ $f=2.14GHz$
- Proven Reliability

DESCRIPTION

SEDI's GaN-HEMT offers high efficiency, ease of matching, greater consistency and broad bandwidth for high power L-band amplifiers with 50V operation, and gives you higher gain.

This new product is ideally suited for use in 2.1GHz W-CDMA design requirements as it offers high gain, long term reliability and ease of use.



ABSOLUTE MAXIMUM RATINGS (Case Temperature $T_c=25^{\circ}C$)

Item	Symbol	Condition	Rating	Unit
Operating-Voltage	V_{DS}		55	V
Drain-Source Voltage	V_{DS}	$V_{GS}=-8V$	160	V
Gate-Source Voltage	V_{GS}		-15	V
Total Power Dissipation	P_t		37.5	W
Storage Temperature	T_{stg}		-65 to +175	$^{\circ}C$
Channel Temperature	T_{ch}		250	$^{\circ}C$

RECOMMENDED OPERATING CONDITION

Item	Symbol	Condition	Limit	Unit
DC Input Voltage	V_{DS}		≤ 55	V
Forward Gate Current	I_{GF}	$R_G=15\Omega$	≤ 69	mA
Reverse Gate Current	I_{GR}	$R_G=15\Omega$	≥ -1.1	mA
Channel Temperature	T_{ch}		≤ 180	$^{\circ}C$
Average Output Power	$P_{ave.}$		≤ 42.0	dBm

ELECTRICAL CHARACTERISTICS (Case Temperature $T_c=25^{\circ}C$)

Item	Symbol	Condition	Limit			Unit
			min.	Typ.	Max.	
Pinch-Off Voltage	V_p	$V_{DS}=50V$ $I_{DS}=7.8mA$	-1.0	-1.5	-2.0	V
Saturated Power	$P_{sat} *1$	$V_{DS}=50V$	44.0	45.0	-	dBm
Drain Efficiency	$\eta_d *2$	$I_{DS}(DC)=150mA$	10.5	12.5	-	%
Power Gain	$G_p *2$	$f=2.14GHz$	18.0	19.0	-	dB
Thermal Resistance	R_{th}	Channel to Case at 24W P_{DC}	-	5.0	6.0	$^{\circ}C/W$

*1 : 10%-duty RF pulse (DC supply constant)

*2 : $P_{out} = 31.5dBm$, CW



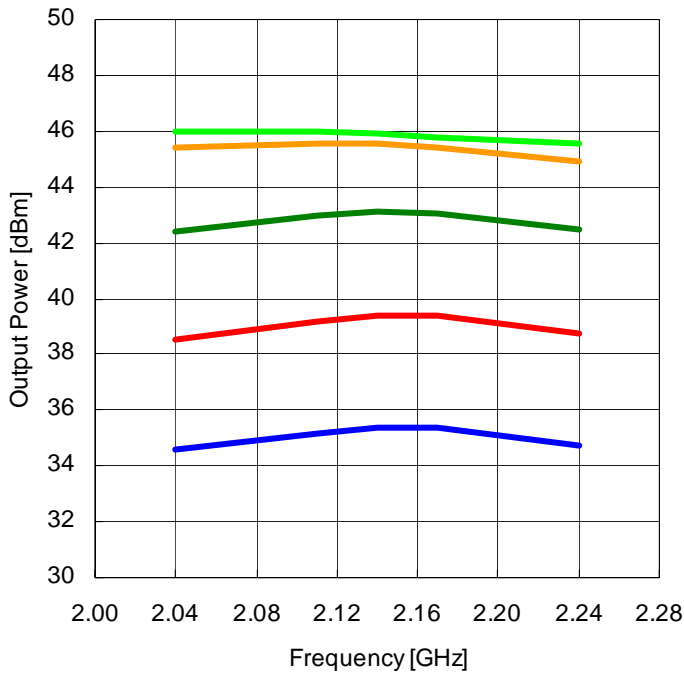
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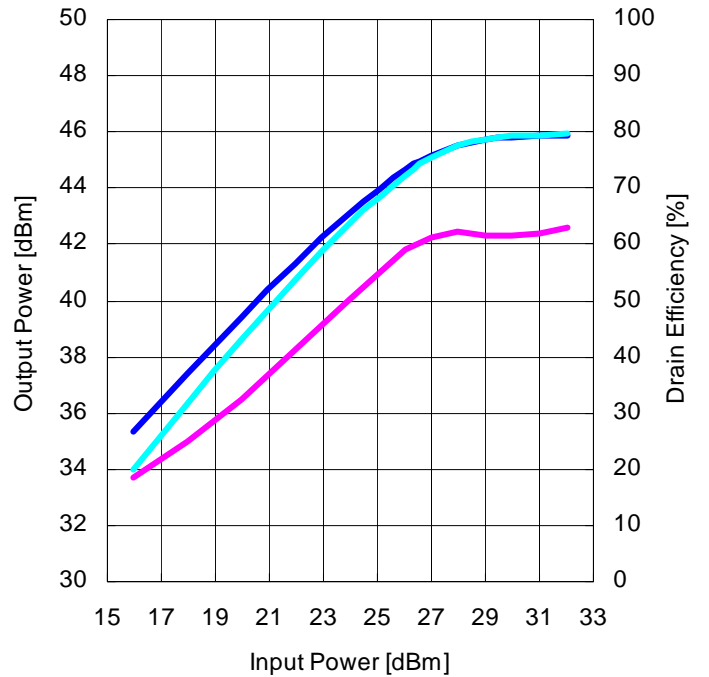
RF characteristics @f=2.14GHz fine tuned

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Output Power vs. Frequency
V_{DS}=50V, I_{DS(DC)}=150mA



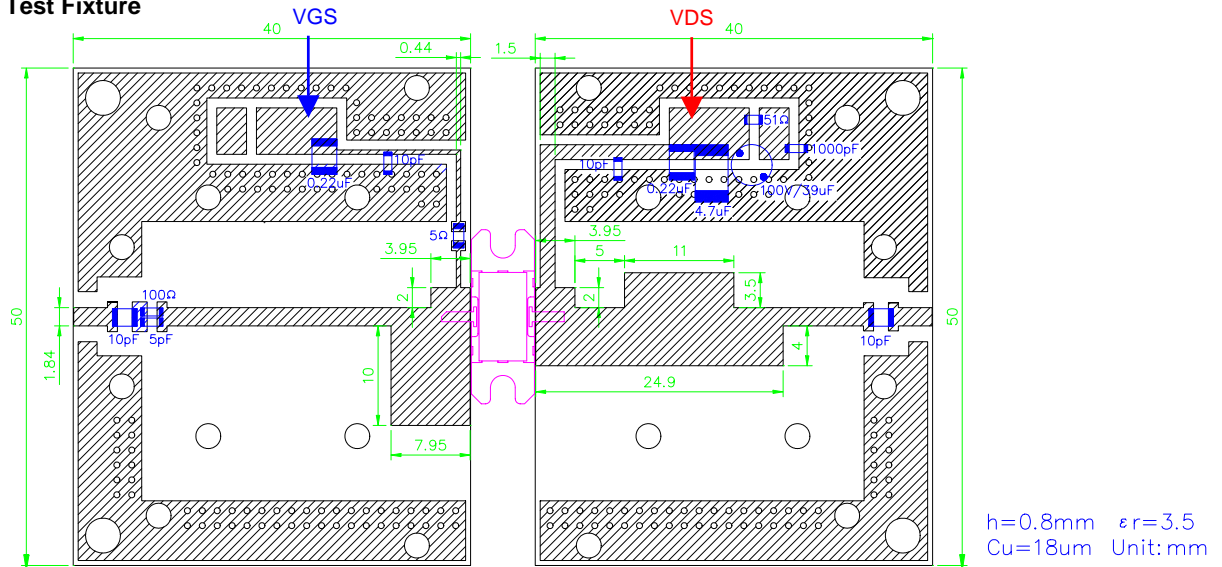
Output Power and Drain Efficiency vs. Input Power
V_{DS}=50V, I_{DS(DC)}=150mA, f=2.14GHz



Pin=16dBm Pin=20dBm Pin=24dBm
Pin=28dBm Pin=32dBm

Pout (class AB) Pout (class B) Nd (class B)

Test Fixture



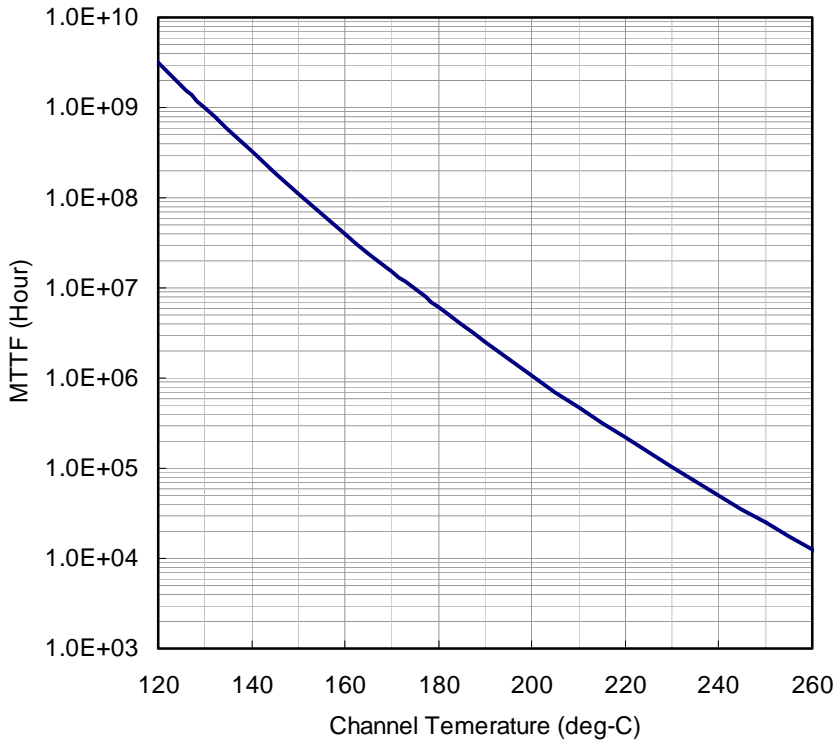


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MTTF Calculation
- Estimated MTTF -



Ea=1.6eV
Confidence Level=90%

Channel Temp (deg-C)	MTTF (Hours)
160	4.05 x 10 ⁷
180	6.07 x 10 ⁶
200	1.07 x 10 ⁶

$$AF = \exp\left[-\frac{Ea}{k}\left(\frac{1}{T_{stress}} - \frac{1}{T_{use}}\right)\right]$$

$$MTTF_{use} = MTTF_{stress} * AF$$

Where;

AF: acceleration factor

Ea: activation energy (1.6 eV)

k: Boltzman's constant (8.62 x 10⁻⁵ eV/K)

T_{stress}: stress temperature (K)

T_{use}: use temperature (K)

ESD characteristic

Test Methodology	Class
Human Body Model (per JESD22-A114)	0
Machine Model (per JEI/ESD22-A115)	A



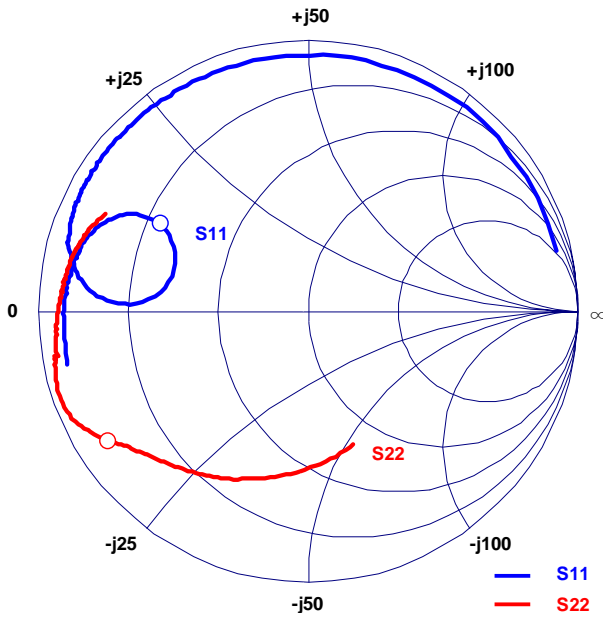
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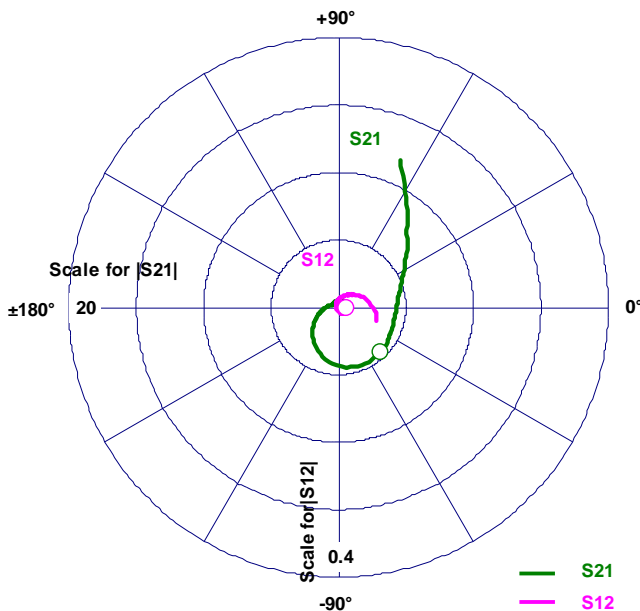
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- Reference DATA -

S-Parameters @V_{DS}=50V, I_{DS(DC)}=150mA, f=0.5 to 5.5GHz
Z_I = Z_s = 50 ohm Marker : 2.14GHz



Freq. GHz	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
0.50	0.92	-167.76	11.88	67.33	0.007	-1.05	0.52	-71.31
0.60	0.91	-172.44	9.91	60.12	0.008	-9.94	0.55	-79.39
0.70	0.91	-176.35	8.50	53.22	0.007	-8.07	0.57	-87.12
0.80	0.91	-179.64	7.40	46.87	0.007	-10.93	0.60	-94.46
0.90	0.90	-177.22	6.61	39.83	0.007	-8.43	0.62	-101.38
1.00	0.90	-174.37	5.93	34.28	0.007	-5.18	0.65	-107.51
1.10	0.90	-172.14	5.46	28.05	0.006	-8.73	0.68	-112.74
1.20	0.89	-169.65	5.09	22.56	0.006	-11.64	0.70	-117.63
1.30	0.88	-167.20	4.78	16.88	0.005	-8.15	0.71	-122.04
1.40	0.88	-164.80	4.53	10.93	0.006	3.38	0.73	-126.03
1.50	0.87	-162.30	4.38	4.93	0.007	7.18	0.75	-129.81
1.60	0.85	-160.12	4.27	-1.03	0.007	-0.84	0.77	-133.16
1.70	0.84	-157.53	4.21	-7.87	0.007	7.36	0.79	-136.27
1.80	0.81	-155.22	4.21	-14.31	0.008	2.46	0.80	-139.10
1.90	0.78	-152.62	4.27	-22.78	0.008	5.59	0.82	-141.54
2.00	0.73	-150.55	4.35	-31.36	0.008	-2.59	0.84	-144.10
2.10	0.67	-149.70	4.49	-41.55	0.010	-6.62	0.86	-145.87
2.20	0.60	-150.44	4.58	-53.44	0.011	-17.62	0.90	-148.41
2.30	0.54	-156.11	4.58	-68.01	0.011	-26.30	0.92	-151.11
2.40	0.52	-165.55	4.47	-82.96	0.011	-34.31	0.95	-153.98
2.50	0.57	-174.45	4.09	-100.02	0.012	-53.88	0.97	-157.62
2.60	0.66	-177.90	3.58	-115.25	0.009	-67.79	0.97	-161.15
2.70	0.75	-177.13	3.04	-128.27	0.008	-87.49	0.97	-164.01
2.80	0.81	-174.57	2.53	-138.81	0.006	-89.61	0.96	-166.41
2.90	0.86	-171.89	2.14	-148.70	0.005	-103.89	0.96	-168.36
3.00	0.89	-168.51	1.79	-155.37	0.004	-137.30	0.95	-170.12
3.10	0.91	-166.09	1.53	-162.57	0.003	-132.30	0.95	-171.70
3.20	0.93	-163.76	1.32	-167.51	0.002	-171.39	0.94	-173.24
3.30	0.94	-160.96	1.15	-172.75	0.003	-179.32	0.94	-174.55
3.40	0.94	-158.76	1.01	-177.44	0.003	-139.32	0.94	-175.89
3.50	0.95	-156.39	0.90	-178.06	0.003	-132.52	0.93	-177.18
3.60	0.95	-154.54	0.81	-175.02	0.005	-127.36	0.93	-178.48
3.70	0.95	-152.38	0.73	-170.36	0.005	-122.70	0.93	-179.59
3.80	0.95	-150.32	0.68	-167.48	0.006	-112.99	0.93	-179.18
3.90	0.95	-147.92	0.63	-163.44	0.007	-102.76	0.92	-177.96
4.00	0.95	-145.49	0.58	-160.11	0.009	-106.05	0.92	-176.76
4.10	0.95	-143.02	0.56	-156.87	0.010	-95.65	0.92	-175.67
4.20	0.95	-140.18	0.52	-152.60	0.011	-87.44	0.91	-174.45
4.30	0.95	-137.45	0.51	-149.28	0.013	-86.12	0.91	-173.35
4.40	0.95	-133.74	0.49	-145.93	0.015	-77.51	0.91	-172.11
4.50	0.95	-129.79	0.48	-140.55	0.017	-73.28	0.91	-170.84
4.60	0.95	-124.99	0.48	-136.95	0.020	-66.34	0.90	-169.42
4.70	0.95	-120.07	0.48	-131.34	0.021	-58.68	0.90	-168.05
4.80	0.95	-113.93	0.48	-126.35	0.024	-52.95	0.90	-166.61
4.90	0.95	-106.51	0.50	-120.05	0.027	-44.93	0.89	-165.05
5.00	0.95	-97.54	0.50	-113.46	0.031	-37.57	0.89	-163.57
5.10	0.95	-86.55	0.53	-105.86	0.036	-28.40	0.88	-161.77
5.20	0.95	-73.45	0.55	-96.22	0.041	-19.22	0.87	-160.12
5.30	0.95	-56.67	0.57	-85.88	0.047	-7.98	0.86	-158.23
5.40	0.94	-37.29	0.60	-71.99	0.053	-4.75	0.85	-156.31
5.50	0.95	-13.73	0.60	-58.10	0.060	-19.80	0.83	-154.40





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MK Package Outline Metal-Ceramic Hermetic Package

